Transistor

Switching (45V, 6.0A) **SP8K24**

Features

- 1) Built-in G-S Protection Diode.
- 2) Small and Surface Mount Package (SOP8).

Applications

Power switching, DC / DC converter, Inverter

●Structure

Silicon N-channel MOS FET

Packaging dimensions

Package	Taping
Code	TB
Basic ordering unit(pieces)	2500

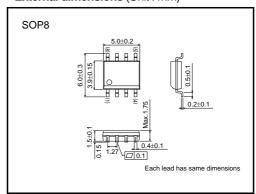
● Absolute maximum ratings (Ta=25°C)

It is the same ratings for the Tr. 1 and Tr. 2.

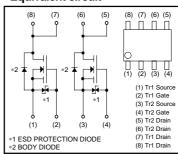
Paramet	Symbol	Limits	Unit		
Drain-source voltage		V_{DSS}	45	V	
Gate-source voltage		V_{GSS}	20	V	
Drain current	Continuous	I_D	±6.0	Α	
	Pulsed	I _{DP}	±24	A *1	
Source current	Continuous	I _S	1	Α	
(Body diode)	Pulsed	I_{SP}	24	A *1	
Total power dissipation		P _D	2	W/TOTAL *2	
		' D	1.4	W/ELEMENT*2	
Chanel temperature		T_{ch}	150	°C	
Range of Storage temperature		T_{stg}	-55 to +150	°C	
*4 DM 40 D					

^{*1} PW \leq 10 μ s, Duty cycle \leq 1%

●External dimensions (Unit : mm)



●Equivalent circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

●Electrical characteristics (Ta=25°C)

It is the same characteristics for the $\mbox{Tr.}\ 1$ and $\mbox{Tr.}\ 2$.

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Gate-source leakage	I _{GSS}	_	_	10	μΑ	$V_{GS}=20V/V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	45	_	_	V	$I_D=1mA/V_{GS}=0V$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS}=45V/V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	_	2.5	V	$V_{DS}=10V/I_{D}=1mA$
Static drain-source on-state resistance	R _{DS(on)} *	_	18	25	mΩ	I _D =6.0A/V _{GS} =10V
		_	24	34		I _D =6.0A/V _{GS} =4.5V
		-	26	37		$I_D = 6.0 \text{A/V}_{GS} = 4.0 \text{V}$
Forward transfer admittance	Y _{fs} *	6.0	_	_	S	$V_{DS}=10V/I_{D}=6.0A$
Input capacitance	C _{iss}	_	1400	_	pF	V _{DS} =10V
Output capacitance	C _{oss}	_	310	_		V _{GS} =0V
Reverce transfer capacitance	C _{rss}	_	175	_		f=1MHz
Turn-on delay time	t _{d(on)} *	ı	19	_	ns	V_{DD} =25 V I_{D} =3.0 A
Rise time	t _r *	ı	30	_		
Turn-off delay time	t _{d(off)} *	ı	72	_		V _{GS} =10V
Fall time	t _f *	_	27	_		$R_L=8\Omega/R_G=10\Omega$
Total gate charge	Q _g *	_	15.4	21.6		$V_{DD} = 25 V/I_{D} = 6.0 A$
Gate-source charge	Q _{gs} *	_	3.7	_	nC	V _{GS} =5V
Gate-drain charge	Q _{gd} *	_	6.5	_		$R_L=4\Omega/R_G=10\Omega$

^{*} pulsed

Body diode characteristics (Source-Drain)

It is the same characteristics for the Tr. 1 and Tr. 2.

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Forward voltage	V _{SD} *	_	_	1.2	V	$I_S=6.0A/V_{GS}=0V$

^{*} pulsed

Electrical characteristic curves

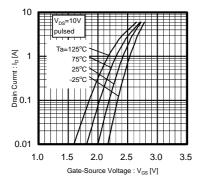


Fig.1 Typical Transfer Characteristics

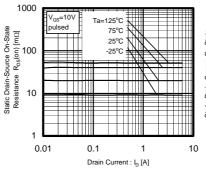


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

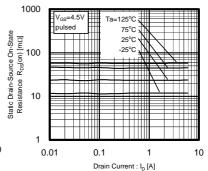


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)

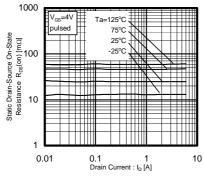


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

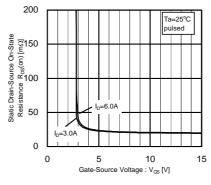


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

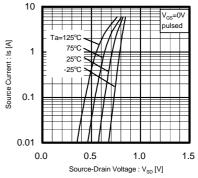


Fig.6 Source-Current vs. Source-Drain Voltage

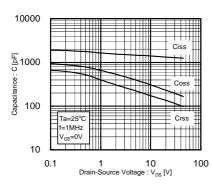


Fig.7 Typical capacitance vs. Source-Drain Voltage

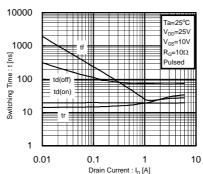


Fig.8 Switching Characteristics

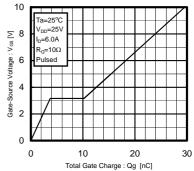


Fig.9 Dynamic Input Characteristics

Measurement circuits

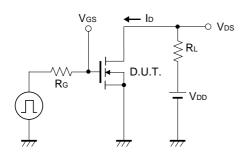


Fig.10 Switching Time Test Circuit

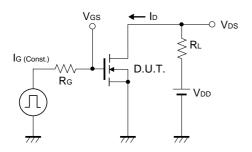


Fig.12 Gate Charge Test Circuit

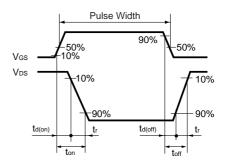


Fig.11 Switching Time Waveforms

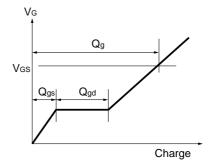


Fig.13 Gate Charge Waveform

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